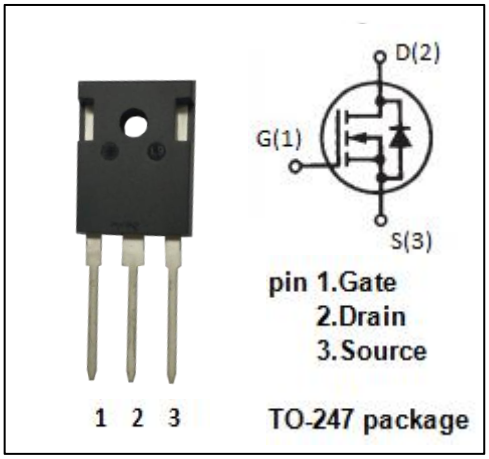


FEATURES

- Drain Current : I_D= 7.8A@ T_C=25℃
- Drain Source Voltage
  : V_{DSS}= 800V(Min)
- Static Drain-Source On-Resistance
  : $R_{DS(on)}$ = 1.2Ω (Max) @ V_{GS}= 10V
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

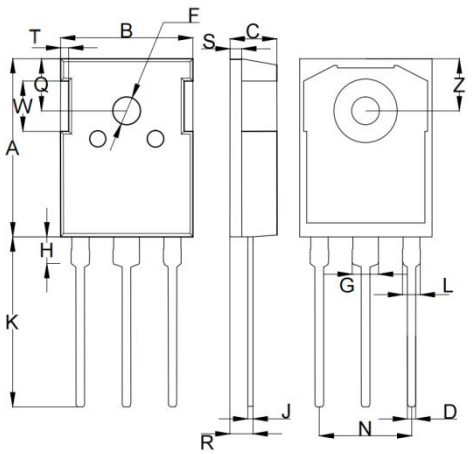
- Switching power supplies,converters,AC and DC motor controls.

• ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	800	V
V_{GS}	Gate-Source Voltage-Continuous	±20	V
I_D	Drain Current-Continuous	7.8	A
I_{DM}	Drain Current-Single Plused	31	A
P_D	Total Dissipation @T_C=25℃	190	W
T_j	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	0.65	℃/W
$R_{\theta JA}$	Junction-to-Ambient	40	℃/W



DIM	mm	
	MIN	MAX
A	19.80	21.50
B	15.40	15.90
C	4.70	5.30
D	0.90	1.26
F	3.50	3.90
G	2.70	3.30
H	3.90	4.10
J	0.500	0.700
K	19.50	20.50
L	1.90	2.20
N	10.80	11.00
Q	6.00	6.30
R	2.90	3.30
S	1.80	2.20
T	2.15	2.35
W	4.90	5.10
Z	6.00	6.30

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 0.25mA	800		V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= 0.25mA	2	4	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 4.7A		1.2	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±20V;V_{DS}= 0		±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 800V; V_{GS}=0		100	uA
V_{SD}	Forward On-Voltage	I_S= 7.8A; V_{GS}=0		1.8	V